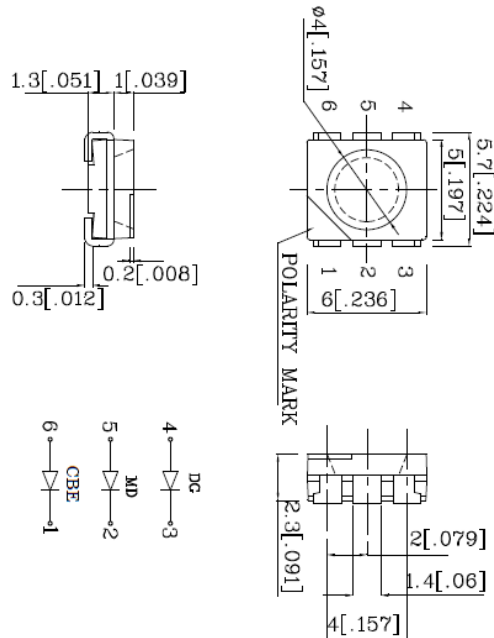


Package Dimensions

P/N: EAF5060PBESEEVGA
5.0x6.0mm SURFACE MOUNT LED LAMP



Notes:

- All dimensions are in millimeters (inches).
- Tolerance is $\pm 0.25(0.01)$ unless otherwise noted.
- Lead spacing is measured where the lead emerge package.
- Specifications are subject to change without notice.

Emitting Color	Emitting Material	Lens-color	Luminous Intensity (IF=30mA *50mA) mcd		Wavelength nm λP	Viewing Angle 2 θ 1/2
			min.	typ.		
Blue	InGaN		180	347	468	
Red	InGaAlP	Water Clear	*380	*497	640	100°
Green	AlInGaN		280	647	515	

Absolute maximum ratings (TA=25°C)		CBE (AlInGa N)	MD (InGaAlP)	DG (AlInGa N)	Unit	Operating Characteristics (TA=25°C)		CBE (AlInGa N)	MD (InGaAlP)	DG (AlInGa N)	Unit
Reverse Voltage	V _R	5	5	5	V	Forward Voltage (Typ.) (IF=20mA)	V _F	3.3	1.9	3.3	V
Forward Current	I _F	30	50	30	mA	Forward Voltage (Max.) (IF=20mA)	V _F	4.0	2.5	4.1	V
Forward Current (Peak) 1/10 Duty Cycle 0.1ms Pulse Width	i _{FS}	150	185	150	mA	Reverse Current (Max.) (V _R =5V)	I _R	10	10	10	uA
Total Power Dissipation Within 350mW at All Chips are Lightened	P _T	350			mW	Wavelength Of Peak Emission (Typ.) (IF=20mA)	λP	468	640	515	nm
Operating Temperature	T _A	-40 ~ +85			°C	Wavelength Of Dominant Emission (Typ.) (IF=20mA)	λD	470	628	525	nm
Storage Temperature	T _{stg}	-40 ~ +85				Spectral Line Full Width At Half-Maximum (Typ.) (IF=20mA)	$\Delta\lambda$	25	27	30	nm
Electrostatic Discharge Threshold (HBM)		1000	-	1000	V	Capacitance (Typ.) (V _F =0V, f=1MHz)	C	100	45	45	pF